FAIRCHILD SEMICONDUCTOR®

August 2006

FDS2734
N-Channel UltraFET Trench® MOSFET
250V, 3.0A, 117mΩ

Features

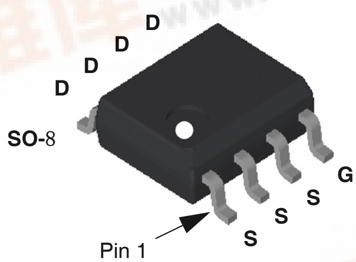
- Max $r_{DS(on)}$ =117mΩ at V_{GS} =10V, I_D = 3.0A
- Max $r_{DS(on)}$ =126mΩ at V_{GS} = 6V, I_D = 2.8A
- Fast switching speed
- High performance trench technology for extremely low $r_{DS(on)}$
- High power and current handling capability
- RoHS compliant

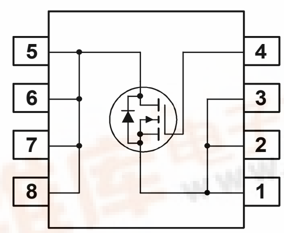
General Descriptions

This single N-Channel MOSFET is produced using Fairchild Semiconductor's advanced UltraFET Trench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Application

- DC-DC conversion





MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DS}	Drain to Source Voltage		250	V
V_{GS}	Gate to Source Voltage		±20	V
I_D	Drain Current -Continuous	(Note 1a)	3.0	A
	-Pulsed		50	
E_{AS}	Single Pulse Avalanche Energy	(Note 3)	12.5	mJ
P_D	Power dissipation	(Note 1a)	2.5	W
	Power dissipation	(Note 1b)	1.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to 150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction- to -Ambient	(Note 1a)	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction- to- Ambient	(Note 1b)	125	
$R_{\theta JC}$	Thermal Resistance, Junction -to- Case	(Note 1)	25	

Package Marking and Ordering Information

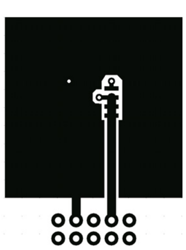
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS2734	FDS2734	SO-8	13''	12mm	2500 units

Electrical Characteristics T_J = 25°C unless otherwise noted

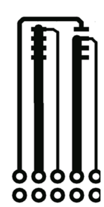
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	250			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		157		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 200V,V_{GS}=0 V			1	μA
		V_{DS} = 200V, V_{GS} = 0V T_J = 55°C			10	
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V, V_{DS} =0 V			±100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	2	3	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		-10.7		mV/°C
$r_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 10V, I_D = 3.0A,		97	117	mΩ
		V_{GS} = 6V , I_D = 2.8A,		101	126	
		V_{GS} = 10V, I_D = 3.0A, T_J = 125°C		205	225	
g_{FS}	Forward Transconductance	V_{DS}=10V, I_D =3.0A,		15.1		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 100V, V_{GS} = 0V, f = 1MHz		1960	2610	pF
C_{oss}	Output Capacitance			85	130	pF
C_{rss}	Reverse Transfer Capacitance			26	40	pF
R_G	Gate Resistance	f = 1MHz		0.7		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 125V, I_D = 3A V_{GS} = 10V, R_{GS} = 6Ω		23	37	ns
t_r	Rise Time			11	19	ns
$t_{d(off)}$	Turn-Off Delay Time			40	64	ns
t_f	Fall Time			11	19	ns
Q_g	Total Gate Charge	V_{DS} = 125V, V_{GS} = 10V I_D = 3.0A		32	45	nC
Q_{gs}	Gate to Source Gate Charge			9		nC
Q_{gd}	Gate to Drain Charge			8		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Voltage	I_{SD} = 3.0A		0.74	1.2	V
t_{rr}	Reverse Recovery Time	I_F = 3.0 A, d_{iF}/dt = 100A/μs		72	108	ns
Q_{rr}	Reverse Recovery Charge			185	278	nC

Notes:

1: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50°C/W when mounted on a 1in^2 pad of 2 oz copper



b) 125°C/W when mounted on a minimum pad of 2 oz copper

Scale 1 : 1 on letter size paper

2: Pulse Test Width <300μs, Duty Cycle <2%.

3: Starting T_J = 25°C, L = 1mH, I_{AS} = 5A, V_{DD} = 100V, V_{GS} = 10V

Typical Characteristics T_J = 25°C unless otherwise noted

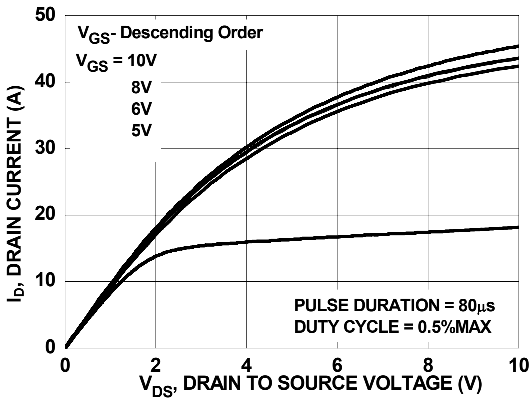


Figure 1. On Region Characteristics

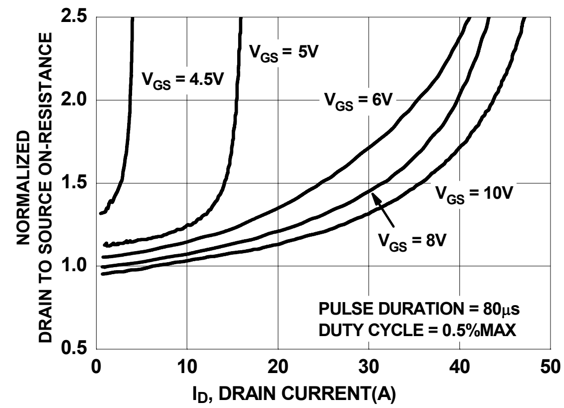


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

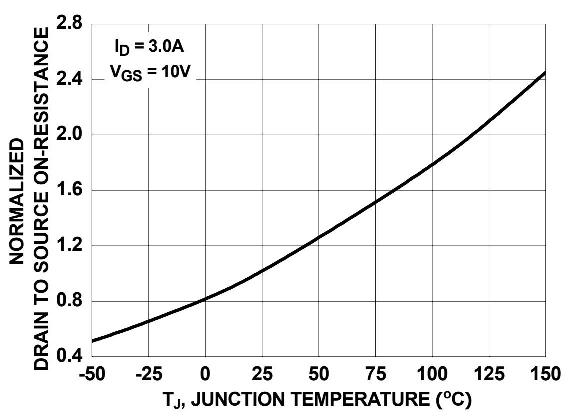


Figure 3. Normalized On Resistance vs Junction Temperature

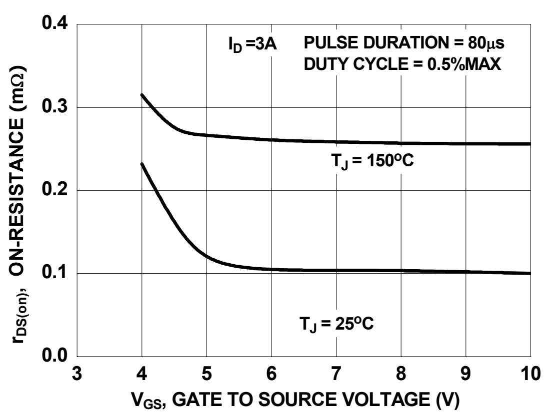


Figure 4. On-Resistance vs Gate to Source Voltage

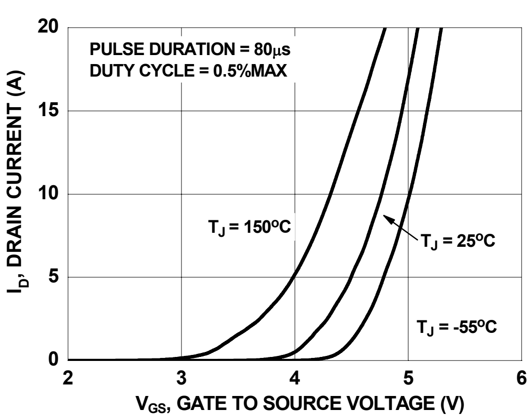


Figure 5. Transfer Characteristics

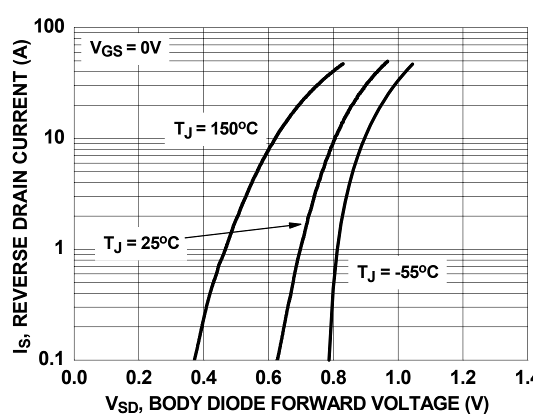


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

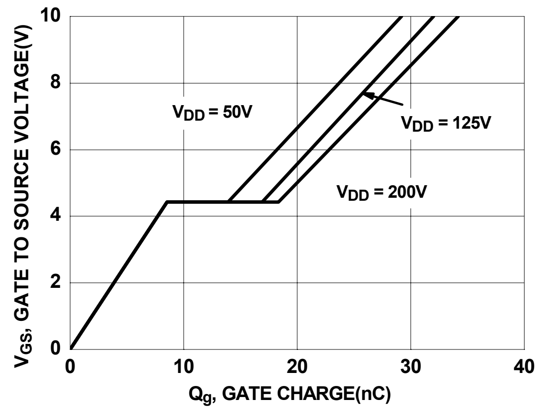


Figure 7. Gate Charge Characteristics

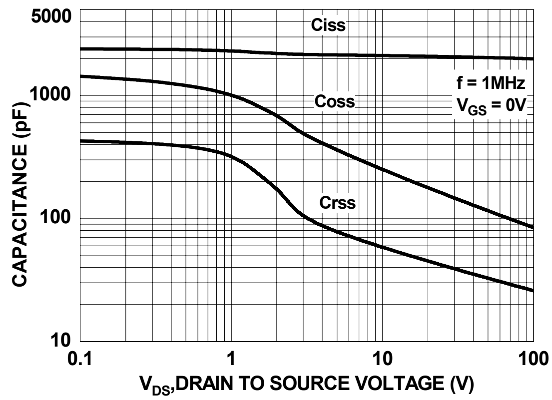


Figure 8. Capacitance vs Drain to Source Voltage

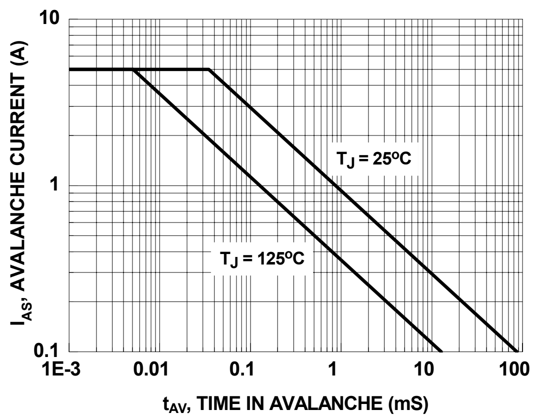


Figure 9. Unclamped Inductive Switching Capability

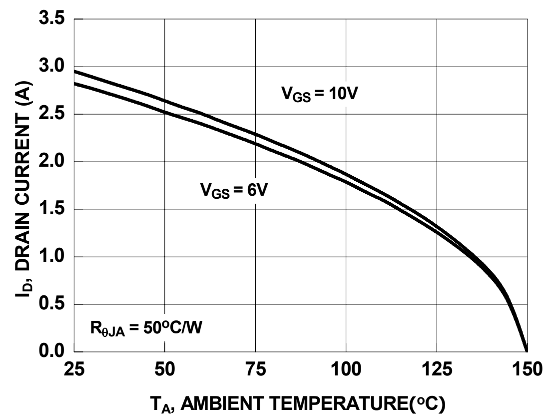


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

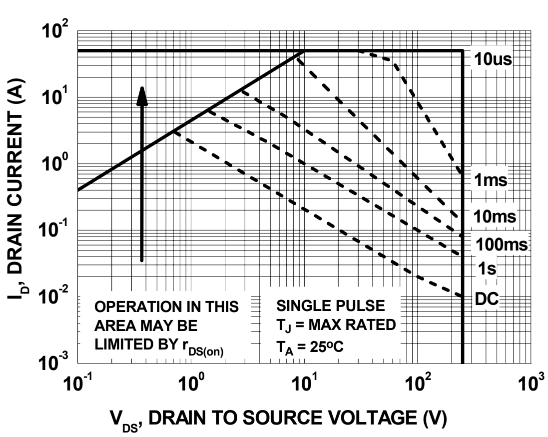


Figure 11. Forward Bias Safe Operating Area

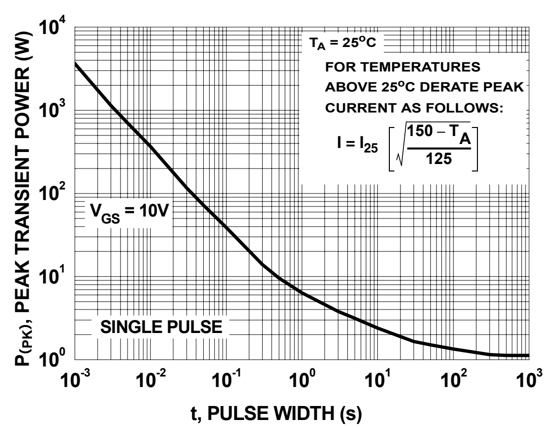


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted

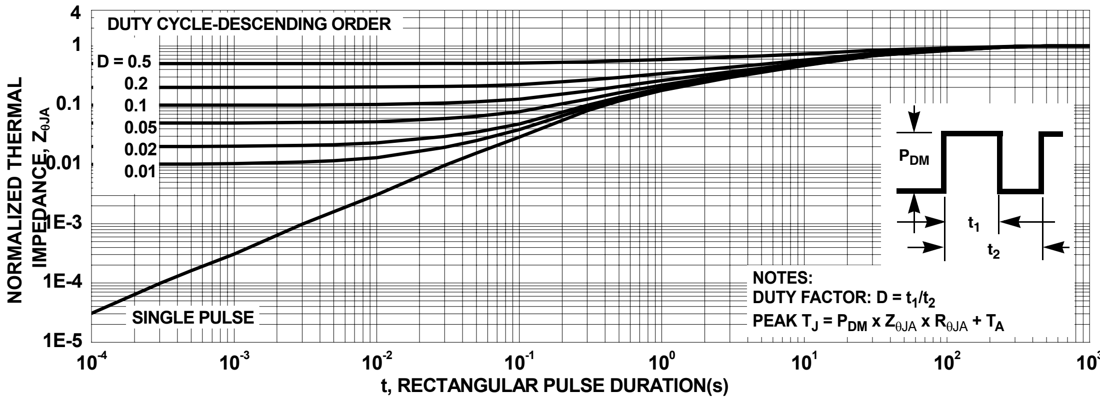


Figure 13. Transient Thermal Response Curve

Thermal characterization performed using the conditions described in Note 1b
Transient thermal response will change depending on the circuit board design

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FACT Quiet Series™	OCX™	SILENT SWITCHER®	UniFET™
ActiveArray™	GlobalOptoisolator™	OCXPro™	SMART START™	UltraFET®
Bottomless™	GTO™	OPTOLOGIC®	SPM™	VCX™
Build it Now™	HiSeC™	OPTOPLANAR™	Stealth™	Wire™
CoolFET™	I^2C™	PACMAN™	SuperFET™	
CROSSVOLT™	*i-Lo*™	POP™	SuperSOT™-3	
DOME™	ImpliedDisconnect™	Power247™	SuperSOT™-6	
EcoSPARK™	IntelliMAX™	PowerEdge™	SuperSOT™-8	
E^2CMOS™	ISOPLANAR™	PowerSaver™	SyncFET™	
EnSigna™	LittleFET™	PowerTrench®	TCM™	
FACT™	MICROCOUPLER™	QFET®	TinyBoost™	
FAST®	MicroFET™	QS™	TinyBuck™	
FASTr™	MicroPak™	QT Optoelectronics™	TinyPWM™	
FPS™	MICROWIRE™	Quiet Series™	TinyPower™	
FRFET™	MSX™	RapidConfigure™	TinyLogic®	
	MSXPro™	RapidConnect™	TINYOPTO™	
Across the board. Around the world.™		µSerDes™	TruTranslation™	
The Power Franchise®		ScalarPump™	UHC™	
Programmable Active Droop™				

DISCLAIMER

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.